

Continental Device India Limited

An ISO/TS 16949, ISO 9001 and ISO 14001 Certified Company



TO-220 Plastic Package

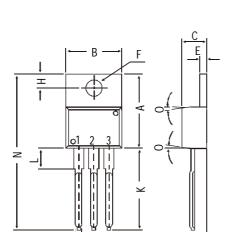
CSC3968

400 V

max.

CSC3968 NPN PLASTIC POWER TRANSISTOR

High Voltage Switching Applications



diminsions in mm.	DIM	MIN.	MAX.
	Α	14.42	16.51
	В	9.63	10.67
	С	3.56	4.83
	D		0.90
	Ε	1.15	1.40
	F	3.75	3.88
	G	2.29	2.79
	Н	2.54	3.43
	J		0.56
	K	12.70	14.73
	L	2.80	4.07
	М	2.03	2.92
	N		31.24
₹	0	DEG 7	

 V_{CBO}

PIN CONFIGURATION
1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

ABSOLUTE MAXIMUM RATINGS Collector-base voltage (open emitter)

Collector-emitter voltage (open base)	$V_{C\!E\!O}$	max.	400 V
Collector current (D.C.)	I_C	max.	2.0 A
Total power dissipation up to $T_C = 25^{\circ}C$	P_{tot}	max.	20 W
Junction temperature	T_{j}	max.	150 °C
Collector-emitter saturation voltage	J		
$I_C = 1A; I_B = 0.2A$	V_{CEsat}	max.	1.0 V
D.C. current gain			
$I_C = 0.1A$; $V_{CE} = 5V$	$h_{\!F\!E}$	min.	16
		max.	<i>50</i>

RATINGS (at T_A =25°C unless otherwise specified) Limiting values

V_{CBO}	max.	400 V
V_{CEO}	max.	400 V
V_{EBO}	max.	7.0 V
I_C	max.	2.0 A
I_C	max.	4.0 A
	V _{CEO} V _{EBO} I _C	V_{CEO} max. V_{EBO} max. I_{C} max.

Total power dissipation up to $T_C = 25^{\circ}C$	P_{tot}	max.	20 W
Total power dissipation up to $T_A = 25^{\circ}C$	P_{tot}	max.	1.5 W
Junction temperature	T_{j}	max.	150 ℃
Storage temperature	T_{stg}	-65 to	+150 ℃
	5.5		
CHARACTERISTICS			
$T_{amb} = 25^{\circ}C$ unless otherwise specified			
Collector cutoff current			
$I_E = 0; \ V_{CB} = 400V$	I_{CBO}	max.	$10 \mu A$
Emitter cut-off current			
$I_C = 0$; $V_{EB} = 7V$	$I_{\!E\!BO}$	max.	$10 \mu A$
Breakdown voltages			
$I_C = 1 \text{ mA}; I_B = 0$	$V_{C\!E\!O}$	min.	400 V
$I_C = 50 \ \mu A; I_E = 0$	V_{CBO}	min.	400 V
$I_E = 50 \ \mu A; I_C = 0$	V_{EBO}	min.	7.0 V
Saturation voltages			
$I_C = 1 A; I_B = 0.2 A$	V_{CEsat}^*	max.	1.0 V
	V_{BEsat}^*	max.	1.5 V
D.C. current gain	DEBut		
$I_C = 0.1A; V_{CE} = 5V^{**}$	$h_{\!F\!E}$	min.	16
C	T.L.	max.	<i>50</i>
Output capacitance at $f = 1$ MHz			
$I_E = 0; \ V_{CB} = 10V$	C_{o}	typ.	30 pF
Transition frequency			
$I_C = 0.5A$; $V_{CE} = 10V$; $f = 5 MHz$	f_T^*	typ.	10 MHz
Switching time			
$I_C = 0.8A; R_L = 250\Omega$			
$I_{B1} = -I_{B2} = 0.08A$			
$V_{CC} = 200V$			
Turn on time	t_{on}	max.	1.0 μs
Storage time	t_{S}	max.	2.5 μs
Fall time	t_f	max.	1.0 μs
	1		•
(1) Single Pulse Pw = 10 ms			
* D 1			

^{**} h_{FE} classification: A: 16-34 B: 25-50

* Pulse test

Customer Notes

Disclaimer

The product information and the selection guides facilitate selection of the CDIL's Discrete Semiconductor Device(s) best suited for application in your product(s) as per your requirement. It is recommended that you completely review our Data Sheet(s) so as to confirm that the Device(s) meet functionality parameters for your application. The information furnished on the CDIL Web Site/CD are believed to be accurate and reliable. CDIL however, does not assume responsibility for inaccuracies or incomplete information. Furthermore, CDIL does not assume liability whatsoever, arising out of the application or use of any CDIL product; neither does it convey any license under its patent rights nor rights of others. These products are not designed for use in life saving/support appliances or systems. CDIL customers selling these products (either as individual Discrete Semiconductor Devices or incorporated in their end products), in any life saving/support appliances or systems or applications do so at their own risk and CDIL will not be responsible for any damages resulting from such sale(s).

CDIL strives for continuous improvement and reserves the right to change the specifications of its products without prior notice.



CDIL is a registered Trademark of Continental Device India Limited

C-120 Naraina Industrial Area, New Delhi 110 028, India.
Telephone + 91-11-2579 6150, 5141 1112 Fax + 91-11-2579 5290, 5141 1119
email@cdil.com www.cdilsemi.com